

• General Description

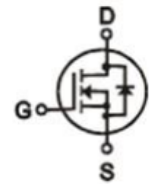
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

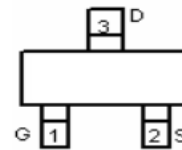
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

• Product Summary


$V_{DS} = -100V$

$R_{DS(ON)} = 360m\Omega$

$I_D = -1.8A$



SOT23-3

• Ordering Information:

Part NO.	ZM036KP10T
Marking	36KP10
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	-1.8	A
	$I_{D@TC=75^\circ C}$	-1.4	A
	$I_{D@TC=100^\circ C}$	-1.1	A
Pulsed Drain Current ①	I_{DM}	-5.4	A
Total Power Dissipation	$P_D@TC=25^\circ C$	1.7	W
Total Power Dissipation	$P_D@TA=25^\circ C$	0.7	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$

**•Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	80	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	180	° C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250uA	-100			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250uA	-1.2		-2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = -100V, V _{GS} = 0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} = -10V, I _D = -1.8A		360	460	mΩ
		V _{GS} = -4.5V, I _D = -1.6A		450	560	mΩ
Forward Transconductance	g _{FS}	V _{DS} = -10V, I _D = -1.0 A		5		s
Source-drain voltage	V _{SD}	I _S = -1.8A			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz	-	835	-	pF
Output capacitance	C _{oss}		-	438	-	
Reverse transfer capacitance	C _{rss}		-	249	-	

•Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = 25V	-	11.2	-	nC
Gate - Source charge	Q _{gs}	I _D = 5A	-	2.2	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 10V	-	1.4	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Fig.1 Power Dissipation Derating Curve

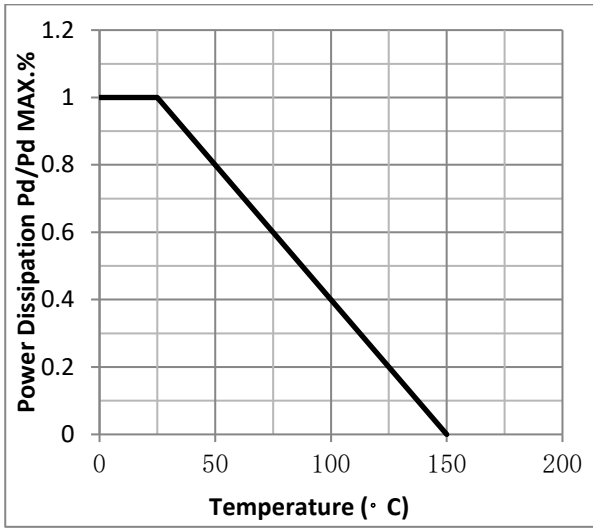


Fig.2 Typical output Characteristics

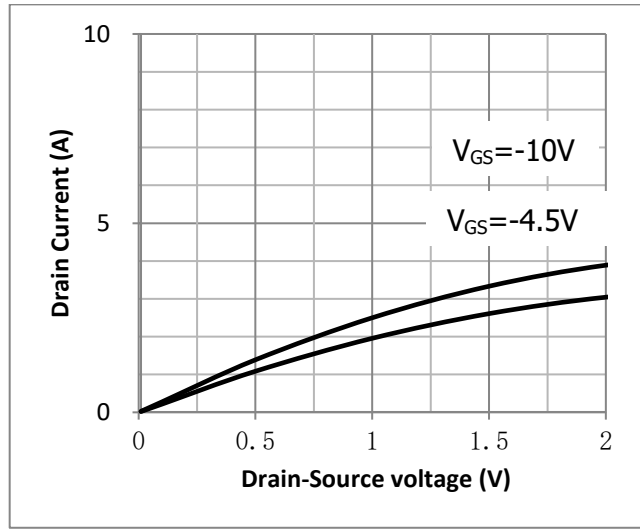


Fig.3 Threshold Voltage V.S Junction Temperature

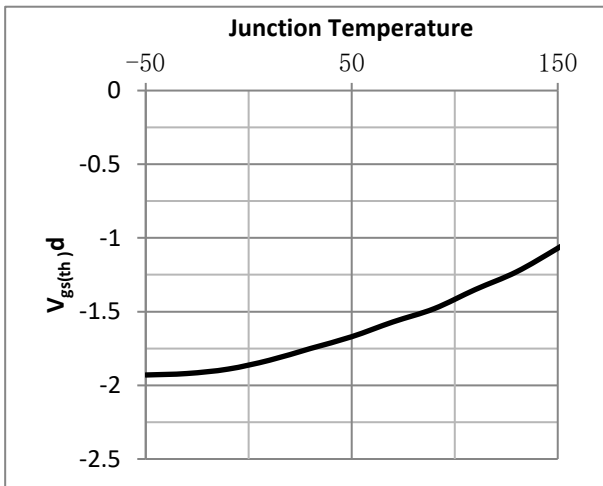


Fig.4 Resistance V.S Drain Current

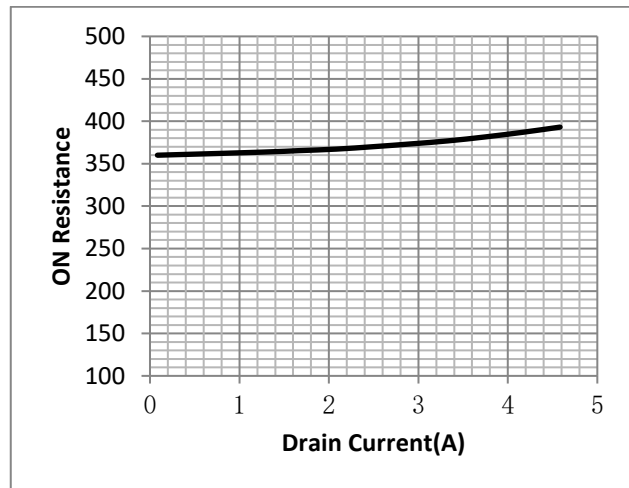


Fig.5 On-Resistance VS Gate Source Voltage

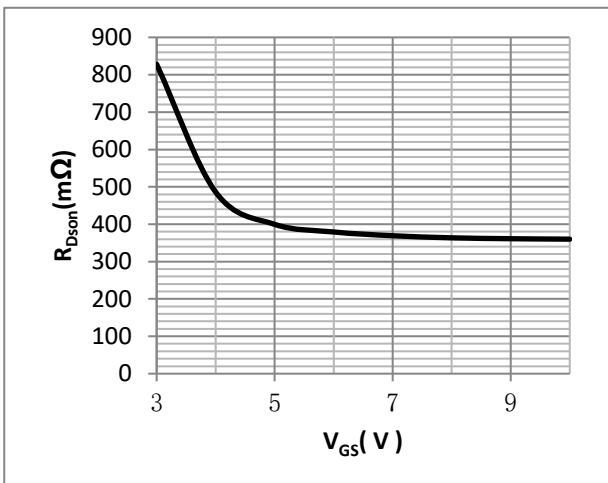


Fig.6 On-Resistance V.S Junction Temperature

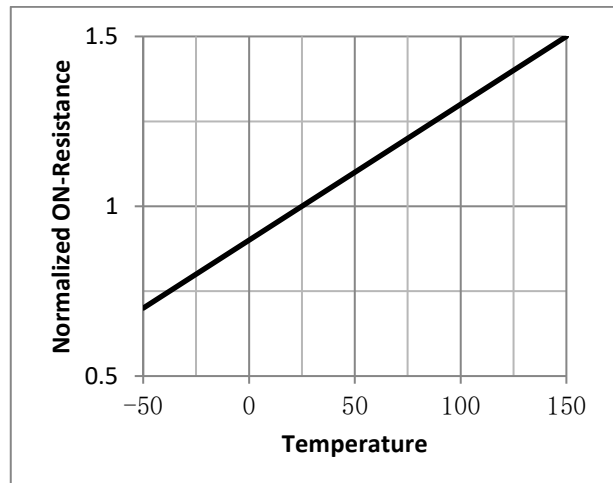


Fig.7 Switching Time Measurement Circuit

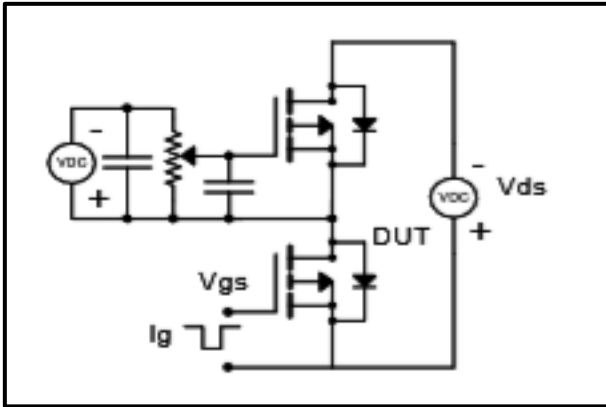


Fig.8 Gate Charge Waveform

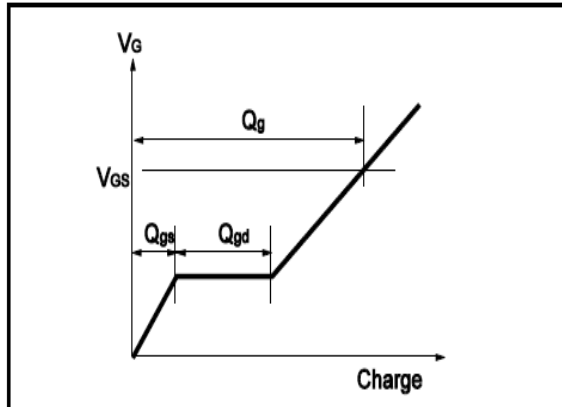


Fig.9 Switching Time Measurement Circuit

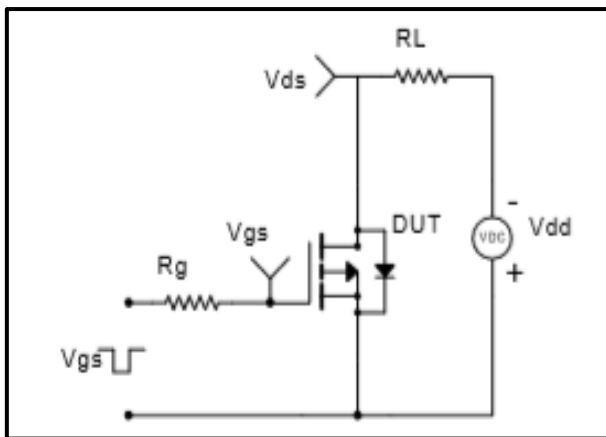


Fig.10 Gate Charge Waveform

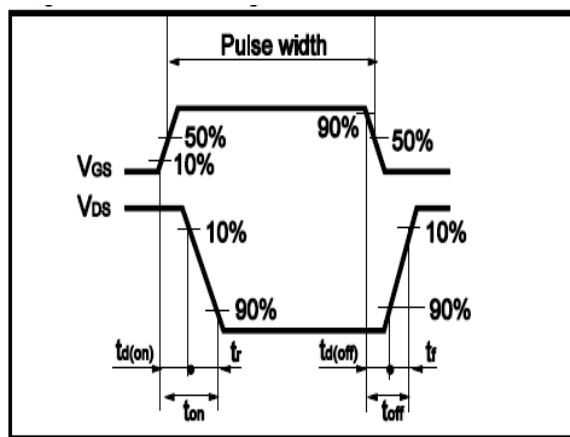


Fig.11 Avalanche Measurement Circuit

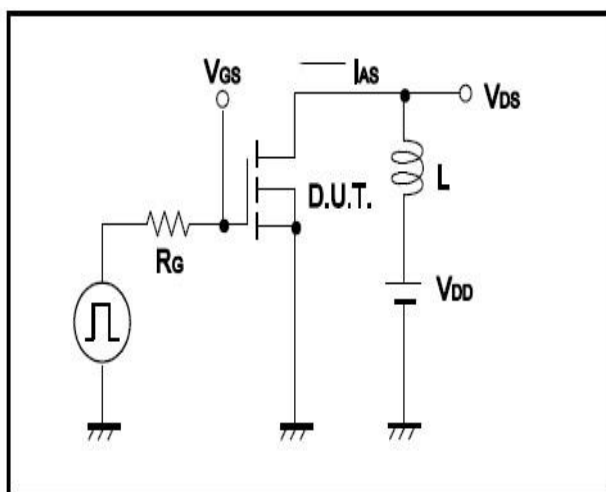
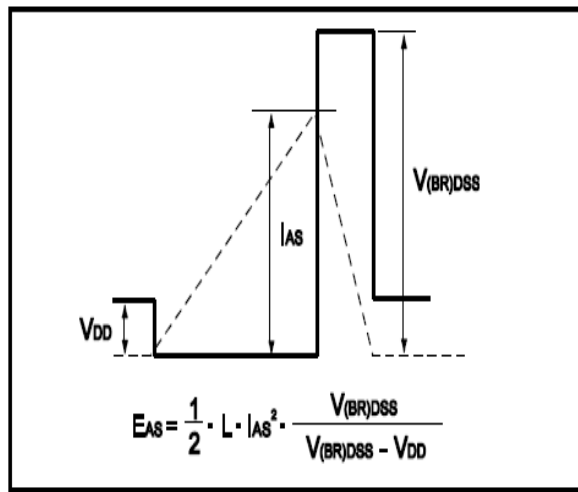


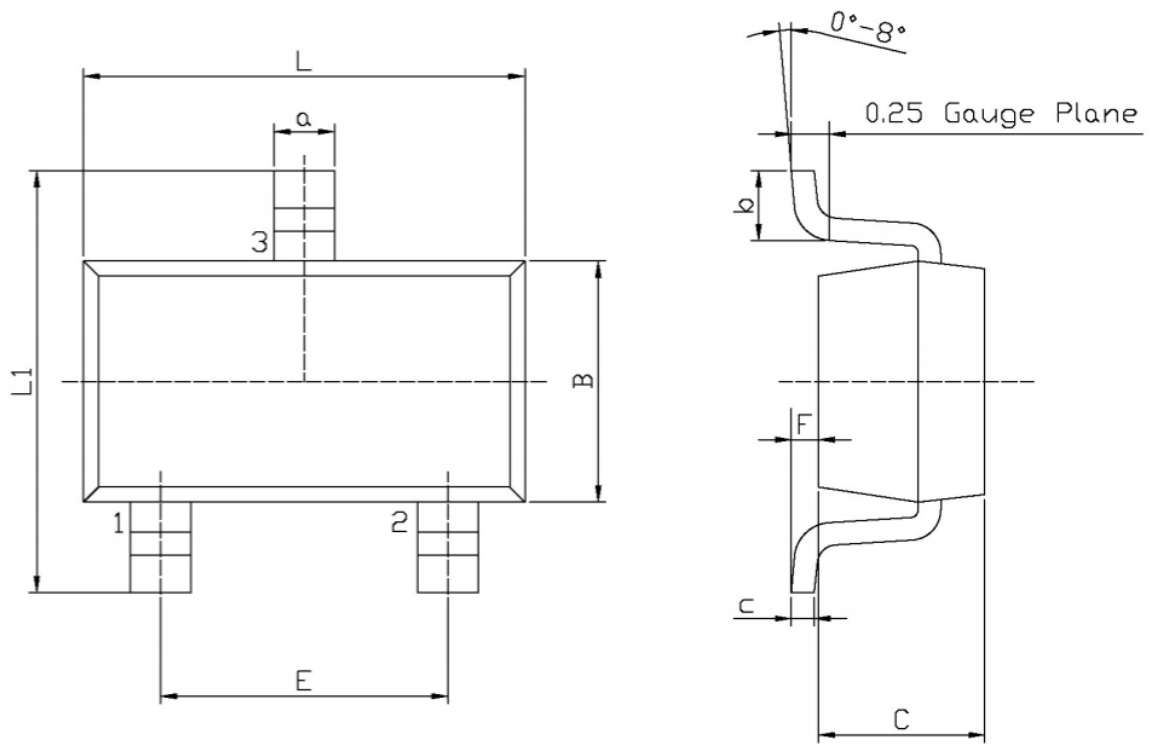
Fig.12 Avalanche Waveform





•Dimensions(SOT23-3)

Unit: mm



Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.82	3.02	a	0.35	0.50
B	1.50	1.70	c	0.10	0.20
C	0.90	1.30	b	0.35	0.55
L1	2.60	3.00	F	0	0.15
E	1.80	2.00			